



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



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Features

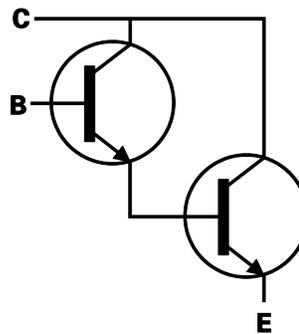
- $BV_{CEO} > 60V$
- $I_{CM} = 800mA$ Peak Pulse Current
- 330mW Power Dissipation
- Darlington Transistor with $h_{FE} > 10k$ at $I_C = 500mA$

Mechanical Data

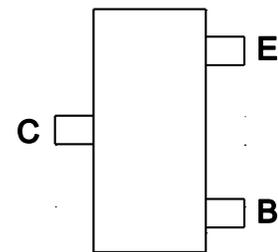
- Case: SOT23
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.008 grams (Approximate)



Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings (@ $T_A = +25^{\circ}\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	10	V
Continuous Collector Current	I_C	300	mA
Peak Pulse Current	I_{CM}	800	mA

Thermal Characteristics (@ $T_A = +25^{\circ}\text{C}$, unless otherwise specified.)

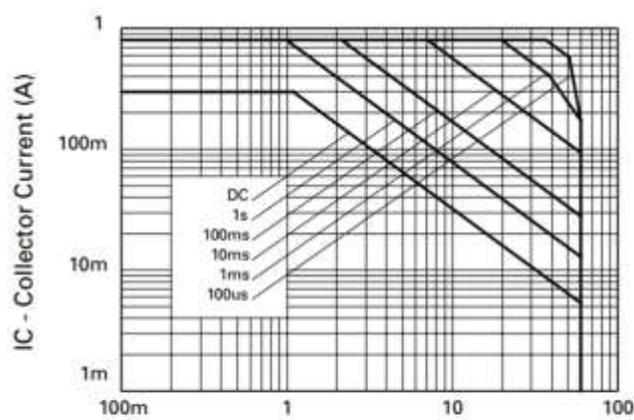
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	330	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	378	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	306	$^{\circ}\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^{\circ}\text{C}$

ESD Ratings (Note 7)

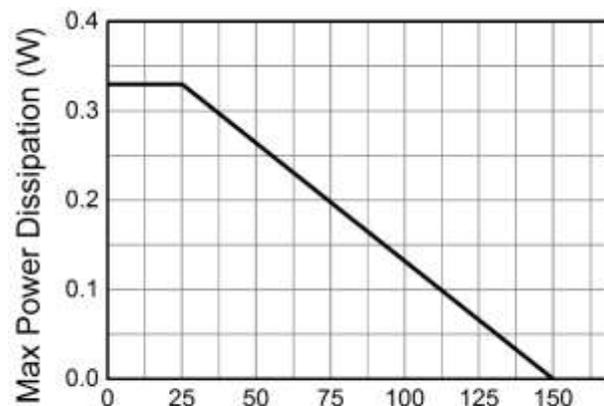
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	2,000	V	2
Electrostatic Discharge – Machine Model	ESD MM	200	V	B

- Notes:
5. For a device mounted on 15mm x 15mm 1oz weight copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 6. Thermal resistance from junction to the top of the case.
 7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

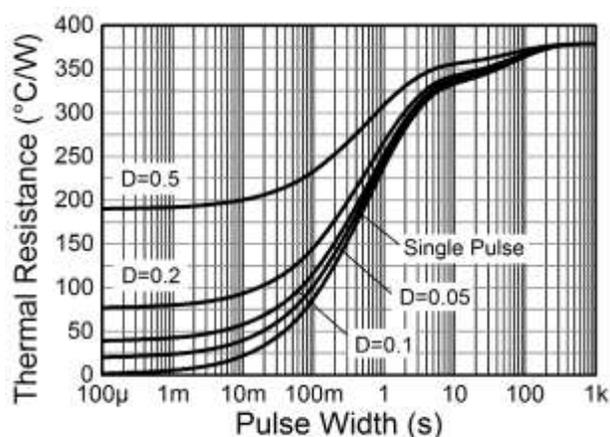
Thermal Characteristics and Derating Information



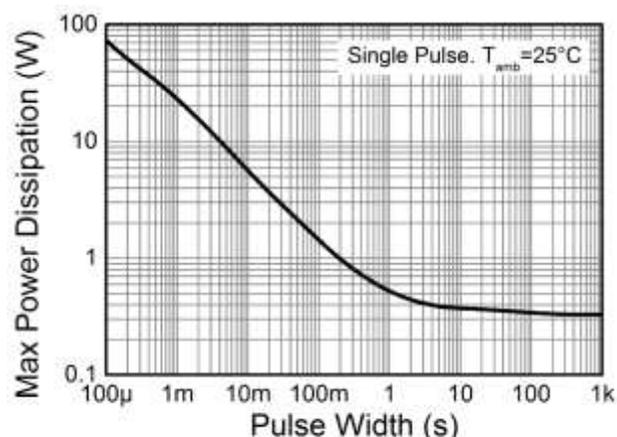
VCE - Collector Emitter Voltage (V)
Safe Operating Area



Temperature (°C)
Derating Curve



Transient Thermal Impedance



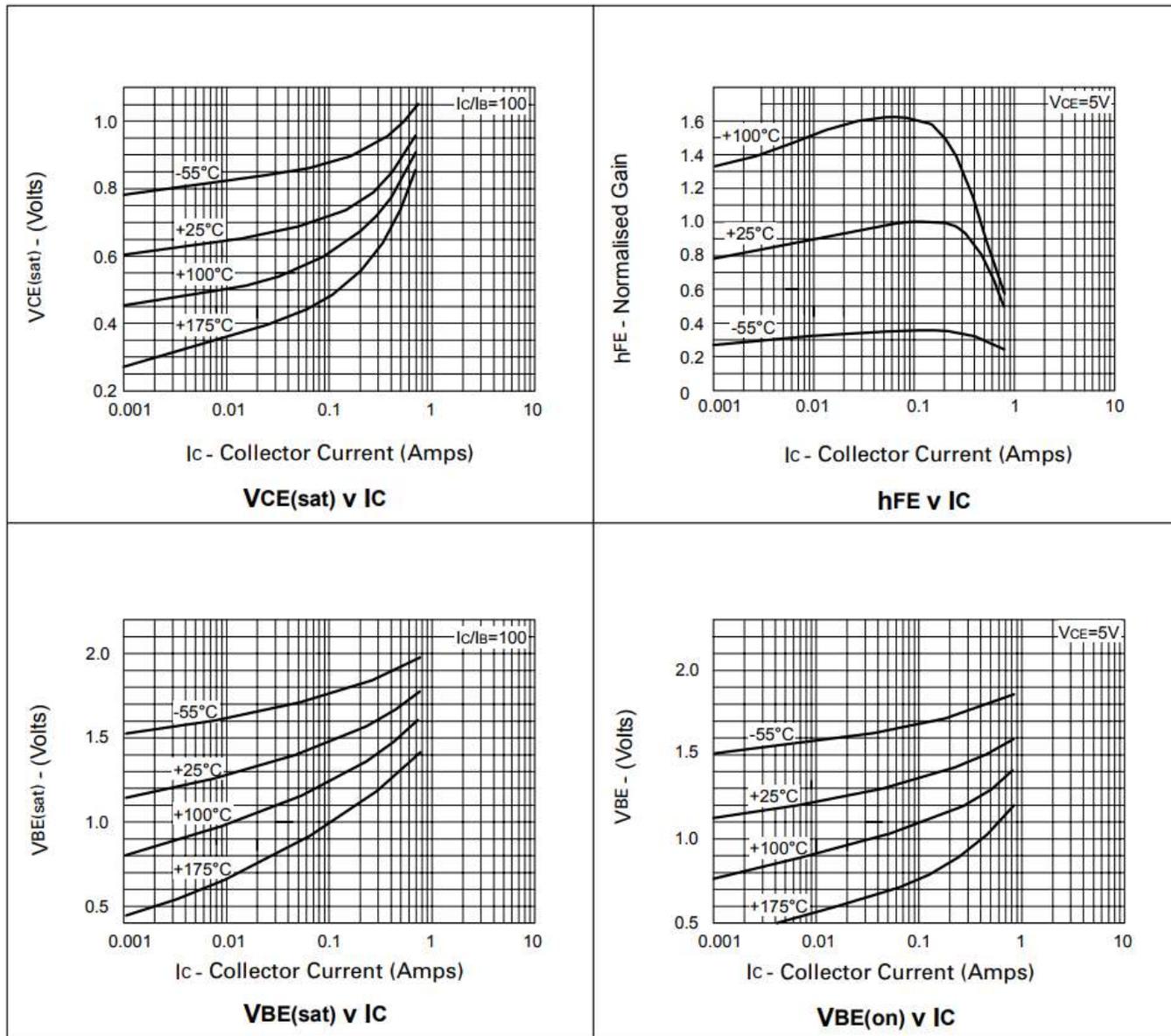
Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CB0}	80	180	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 8)	BV _{CEO}	60	75	—	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	10	16	—	V	I _E = 100μA
Collector Cutoff Current	I _{CBO}	—	1.5	100	nA	V _{CB} = 60V
Emitter Cutoff Current	I _{EBO}	—	1	100	nA	V _{EB} = 8V
Static Forward Current Transfer Ratio (Note 8)	h _{FE}	5k 10k	— 27k	—	—	I _C = 100mA, V _{CE} = 5V I _C = 500mA, V _{CE} = 5V
Collector-Emitter Saturation Voltage (Note 8)	V _{CE(SAT)}	—	0.89	1.25	V	I _C = 800mA, I _B = 8mA
Base-Emitter Turn-On Voltage (Note 8)	V _{BE(ON)}	—	1.3	1.8	V	I _C = 800mA, V _{CE} = 5V

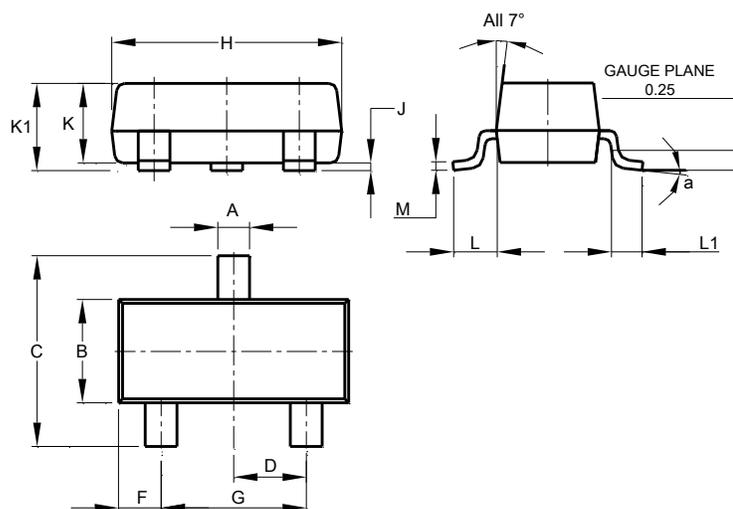
Note: 8. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



Package Outline Dimensions

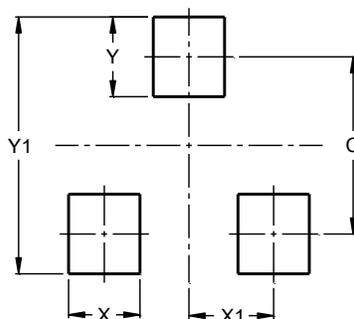
SOT23



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9